

### General Description

The Sanrise SRC60R090B is a high voltage power MOSFET, fabricated using advanced super junction technology. The resulting device has extremely low on resistance, low gate charge and fast switching time, making it especially suitable for applications which require superior power density and outstanding efficiency.

The SRC60R090B break down voltage is 600V and it has a high rugged avalanche characteristics. The SRC60R090B is available in TO-220F and TO-247 packages.

### Features

- Ultra Low  $R_{DS(ON)} = 90m\Omega @ V_{GS} = 10V$ .
- Ultra Low Gate Charge,  $Q_g=90.3nC$  typ.
- Intrinsic Fast-Recovery Body Diode
- Fast switching capability
- Robust design with better EAS performance

### Application

- AC/DC Power Supply
- EV Charger
- PC / Sever / Telecom

### Symbol

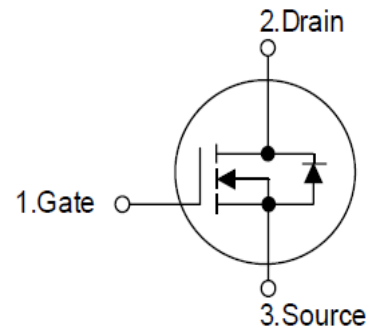


Figure 1 Symbol of SRC60R090B

### Package Type

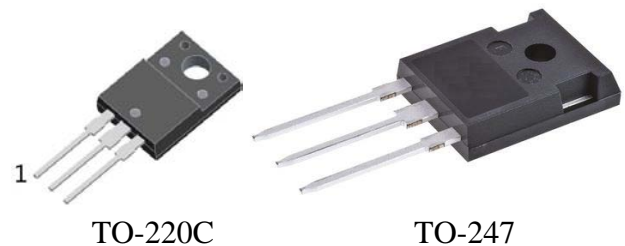
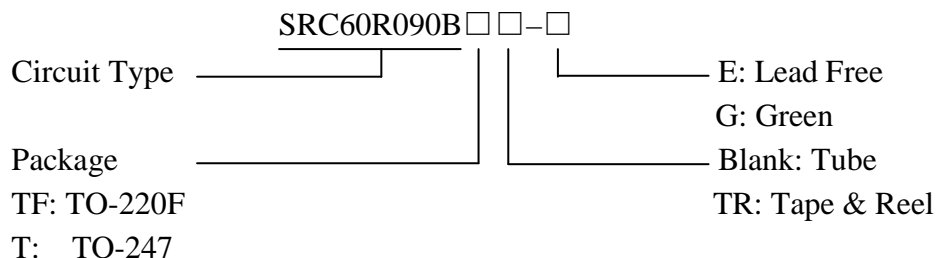


Figure 2 Package Types of SRC60R090B

### Ordering Information



Package	Part Number		Marking ID		Packing Type
	Lead Free	Green	Lead Free	Green	
TO-220F	SRC60R090BTF-E	SRC60R090BTF-G	SRC60R090BTFE	SRC60R090BTFG	Tube
TO-247	SRC60R090BT-E	SRC60R090BT-G	SRC60R090BTE	SRC60R090BTG	Tube

**Absolute Maximum Ratings**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DSS}$	600	V
Gate-Source Voltage	$V_{GSS}$	±30	V
Continuous Drain Current	$I_D$	$T_C=25^{\circ}C$	39.5
		$T_C=125^{\circ}C$	17.8
Pulsed Drain Current (Note 2)	$I_{DM}$	118.5	A
Avalanche Energy, Single Pulse (Note 3)	$E_{AS}$	550	mJ
Avalanche Energy, Repetitive (Note 2)	$E_{AR}$	0.6	mJ
Avalanche Current, Repetitive (Note 2)	$I_{AR}$	4.5	A
Continuous Diode Forward Current	$I_S$	39.5	A
Diode Pulse Current	$I_{S,PULSE}$	118.5	A
MOSFET dv/dt Ruggedness, $V_{DS} \leq 480V$	dv/dt	50	V/ns
Reverse Diode dv/dt, $V_{DS} \leq 480V, I_{SD} \leq I_D$	dv/dt	50	V/ns
Operating Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-55 to 150	°C
Lead Temperature (Soldering, 10 sec)	$T_{LEAD}$	260	°C

Note:

- Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
- Repetitive Rating: Pulse width limited by maximum junction temperature
- $I_{AS} = 4.5A, V_{DD} = 60V, R_G = 25\Omega, \text{Starting } T_J = 25^{\circ}C$

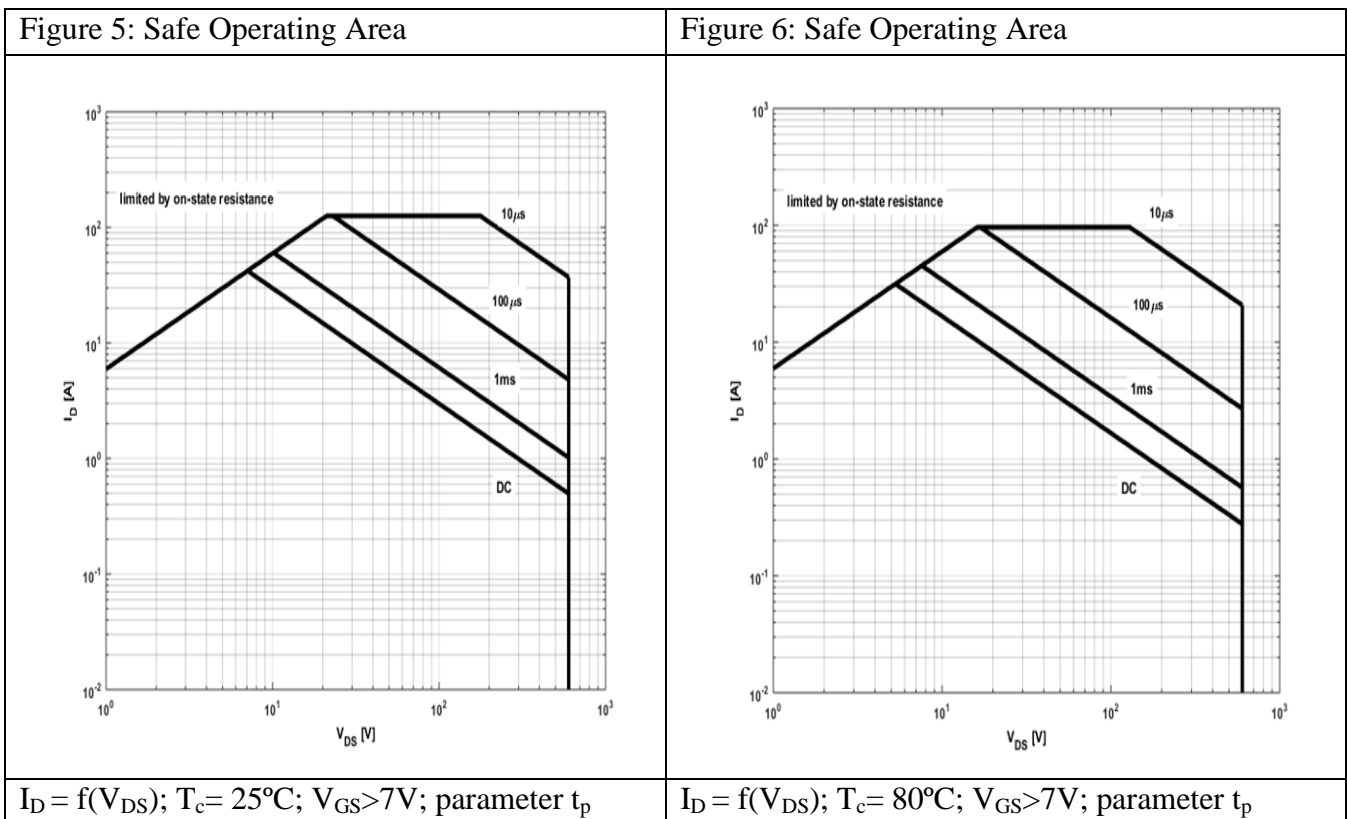
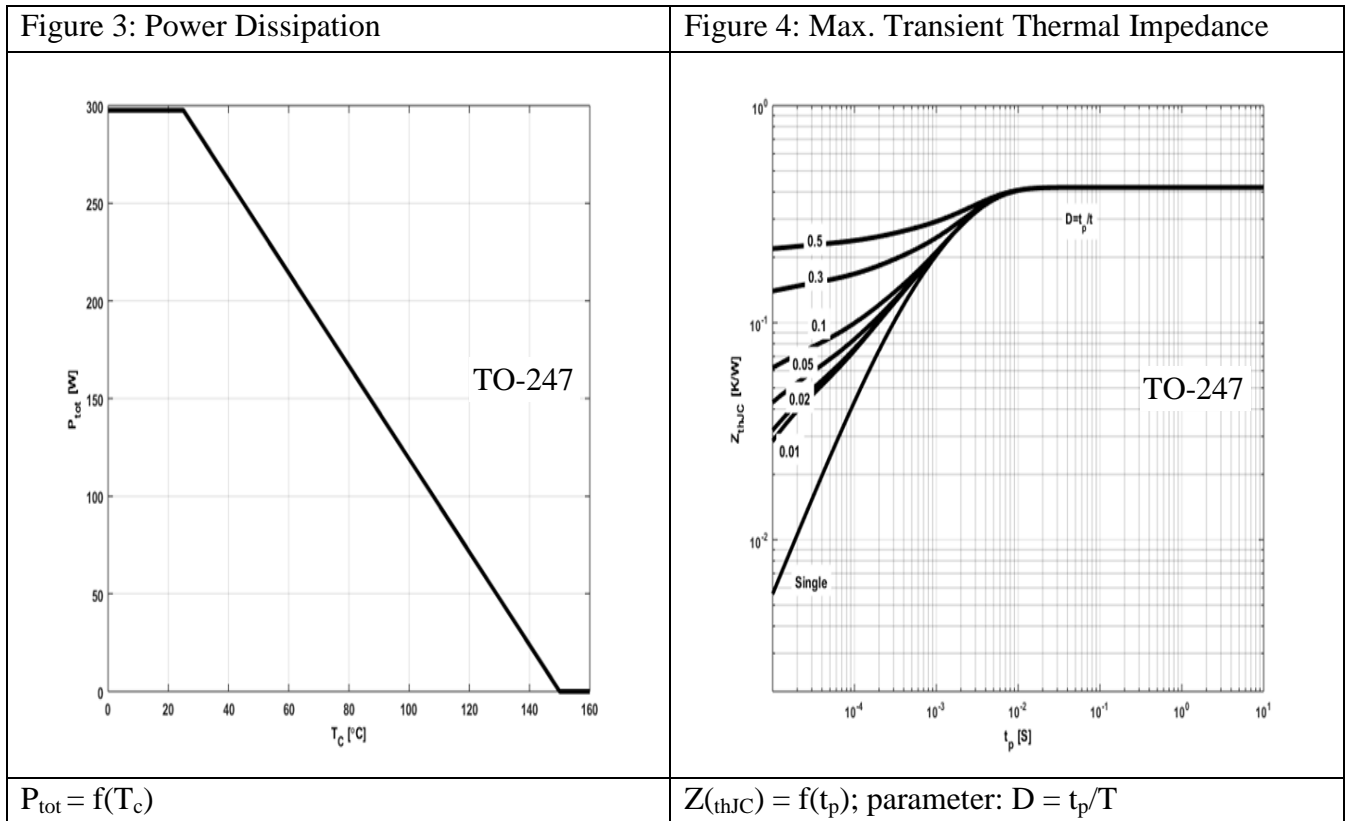
**Electrical Characteristics**
 $T_J = 25^{\circ}\text{C}$ , unless otherwise specified.

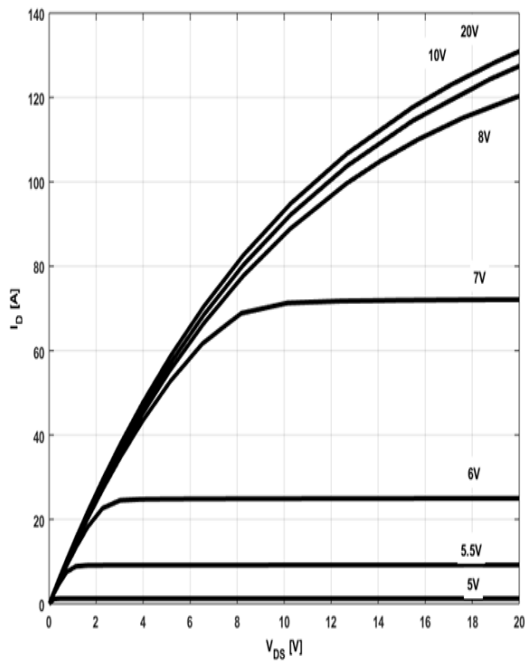
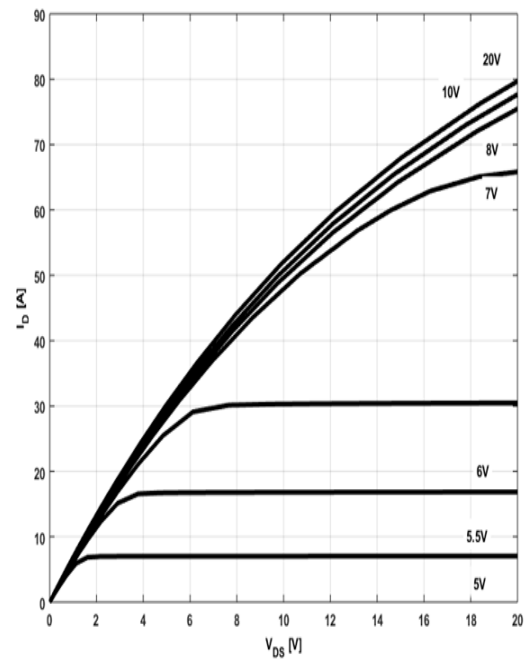
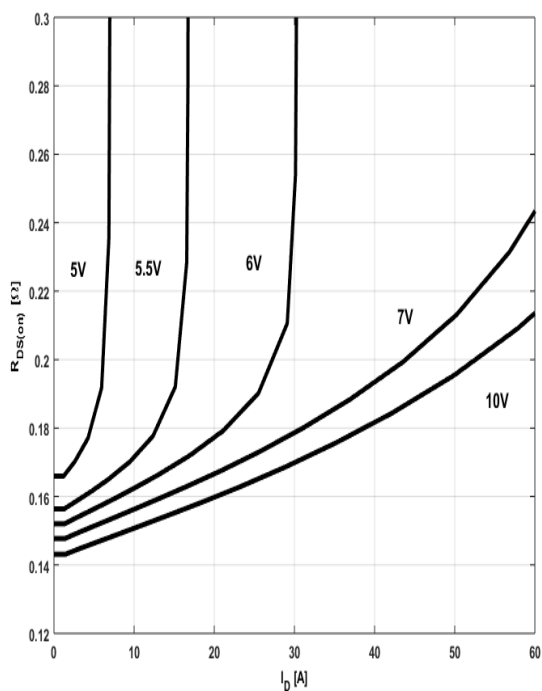
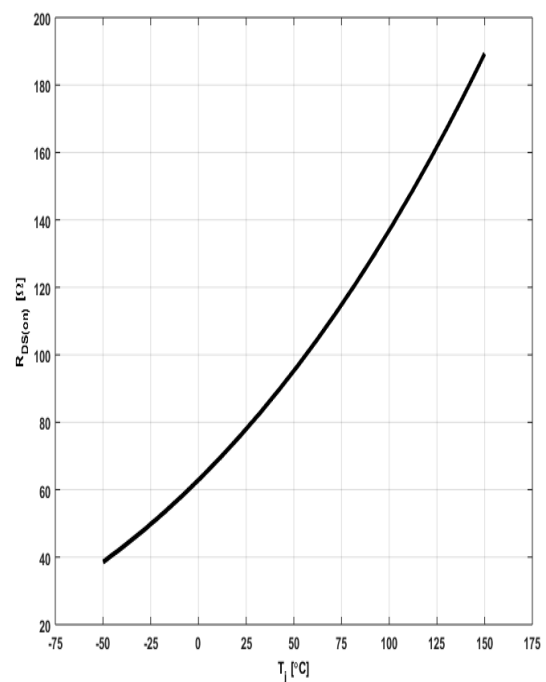
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Statistic Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	600			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=600V, V_{GS}=0V$			10	$\mu A$
Gate-Body Leakage Current	Forward	$I_{GSSF}, V_{GS}=30V, V_{DS}=0V$			100	nA
	Reverse	$I_{GSSR}, V_{GS}=-30V, V_{DS}=0V$			-100	nA
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=800\mu A$	3.5	4.0	4.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$		78	90	mΩ
Gate Resistance	$R_G$	f=1MHz, Open Drain		0.7		Ω
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{ISS}$	$V_{DS}=50V, V_{GS}=0V, f=1MHz$		3300		pF
Output Capacitance	$C_{OSS}$			136		
Reverse Transfer Capacitance	$C_{RSS}$			2.3		
Effective output capacitance, energy related <sup>NOTE5</sup>	$C_{O(er)}$	$V_{GS}=0V, V_{DS}=0\dots 400V$		98.2		pF
Effective output capacitance, time related <sup>NOTE6</sup>	$C_{O(tr)}$			601		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=400V, I_D=20A, R_G=1.8\Omega, V_{GS}=10V$		24		ns
Rise Time	$t_r$			38		
Turn-off Delay Time	$t_{d(off)}$			48		
Fall Time	$t_f$			10		
<b>Gate Charge Characteristics</b>						
Gate to Source Charge	$Q_{gs}$	$V_{DD}=480V, I_D=20A, V_{GS}=0 \text{ to } 10V$		22.9		nC
Gate to Drain Charge	$Q_{gd}$			45.6		
Gate Charge Total	$Q_g$			90.3		
Gate Plateau Voltage	$V_{plateau}$			6.5		V
<b>Reverse Diode Characteristics</b>						
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_{SD}=20A$		0.9	1.1	V
Reverse Recovery Time	$t_{rr}$	$V_R=100V, I_F=20A, dI_F/dt=100A/\mu s$		158		ns
Reverse Recovery Charge	$Q_{rr}$			0.95		$\mu C$
Peak Reverse Recovery Current	$I_{rrm}$			12		A

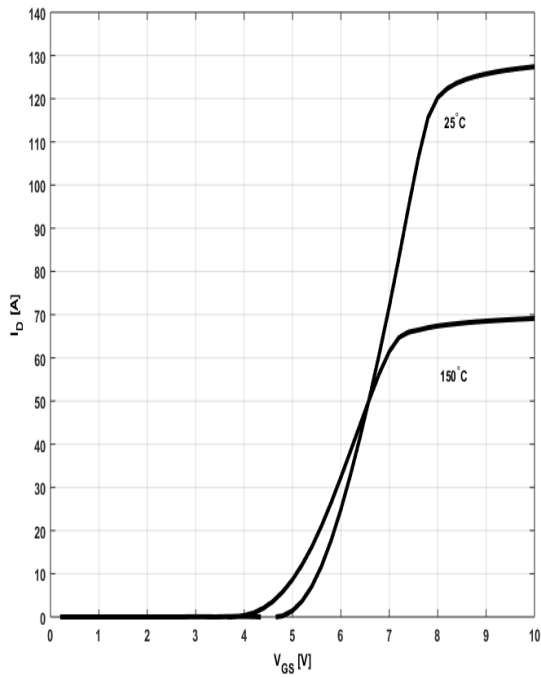
Note:

 5.  $C_{O(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 to 480V

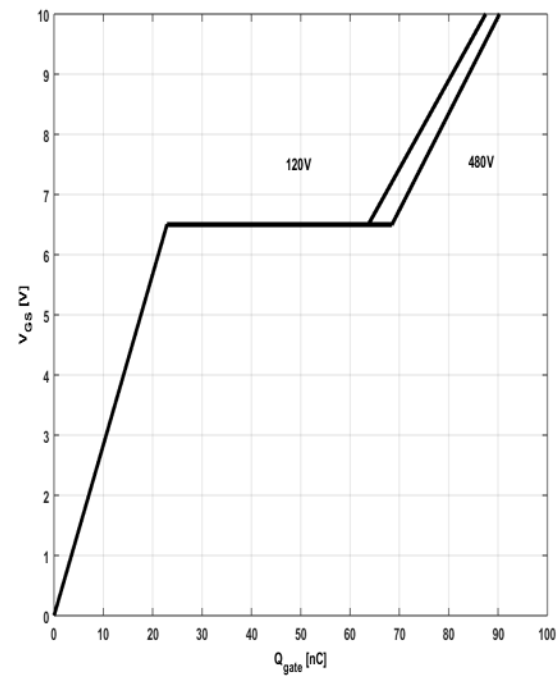
 6.  $C_{O(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 to 480 V

**Typical Performance Characteristics**


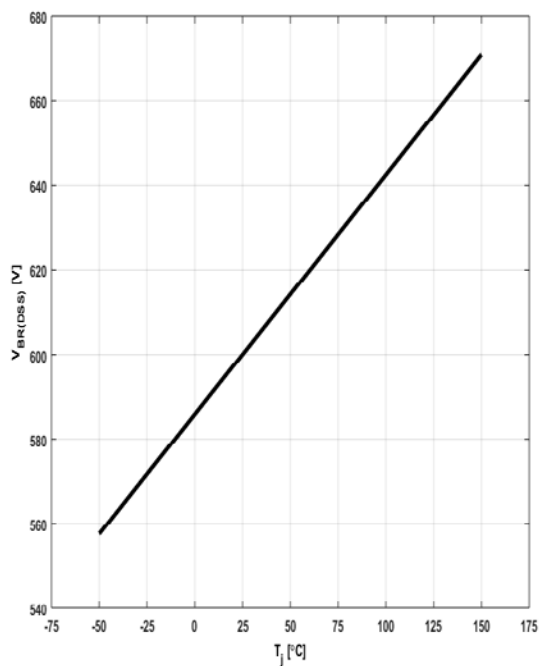
**Figure 7: Typ. Output Characteristics**

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$ 
**Figure 8: Typ. Output Characteristics**

 $I_D = f(V_{DS}); T_j = 125^\circ\text{C}; \text{parameter: } V_{GS}$ 
**Figure 9: Typ. Drain-Source On-State Resistance**

 $R_{DS(ON)} = f(I_D); T_j = 125^\circ\text{C}; \text{parameter: } V_{GS}$ 
**Figure 10: Typ. Drain-Source On-State Resistance**

 $R_{DS(ON)} = f(T_j); I_D = 20\text{A}; V_{GS} = 10\text{V}$

**Figure 11: Typ. Transfer Characteristics**


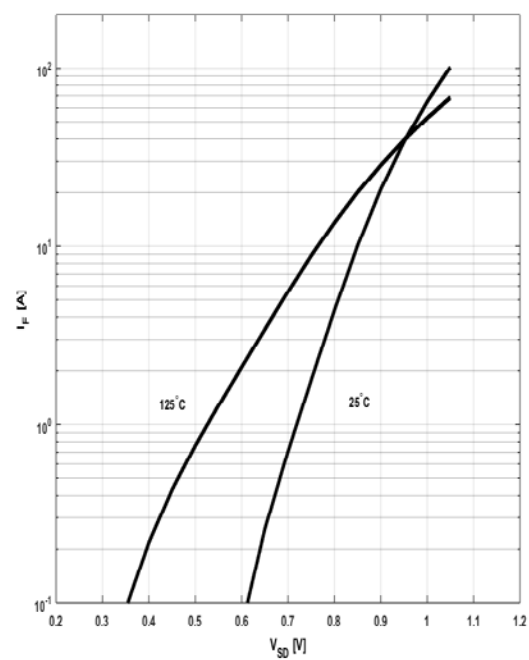
$$I_D = f(V_{GS}); V_{DS} = 20V$$

**Figure 12: Typ. Gate Charge**


$$V_{GS} = f(Q_{gate}), I_D = 20A \text{ pulsed}$$

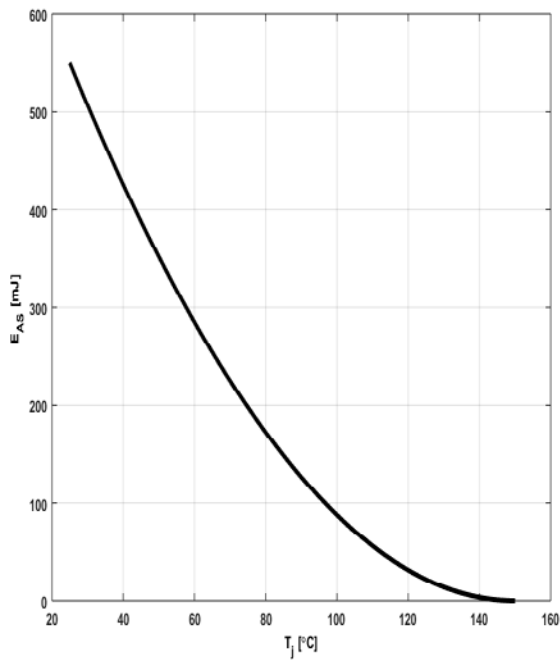
**Figure 13: Drain-Source Breakdown Voltage**


$$V_{BR(DSS)} = f(T_j); I_D = 1mA$$

**Figure 14: Forward Characteristics of Reverse Diode**


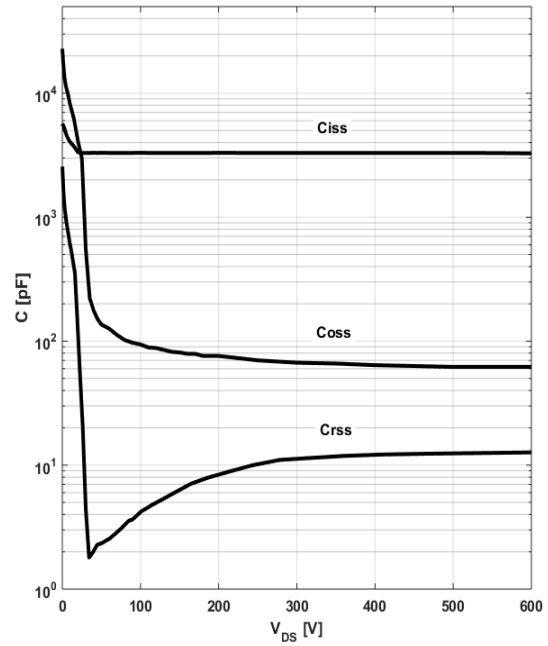
$$I_F = f(V_{SD}); \text{parameter: } T_j$$

Figure 15: Avalanche Energy



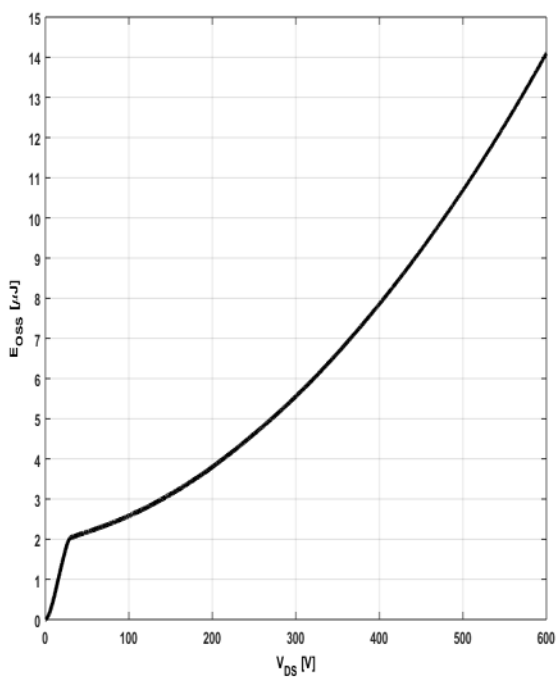
$E_{AS}=f(T_j)$ ;  $I_D=4.5A$ ;  $V_{DD}=60V$

Figure 16: Typ. Capacitances

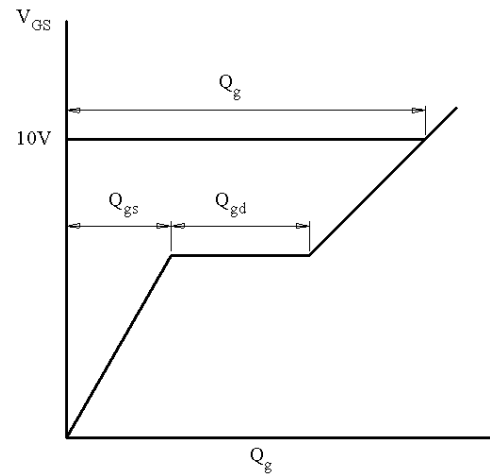
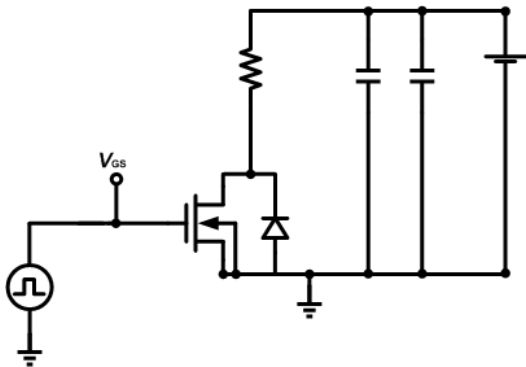
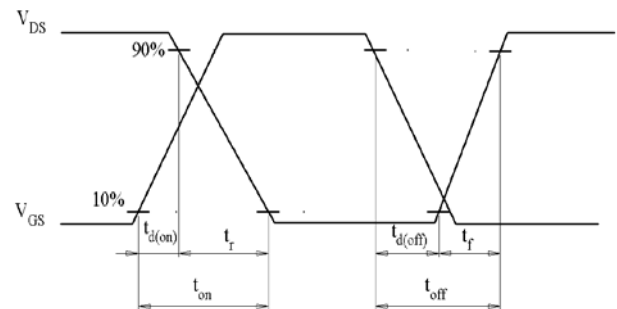
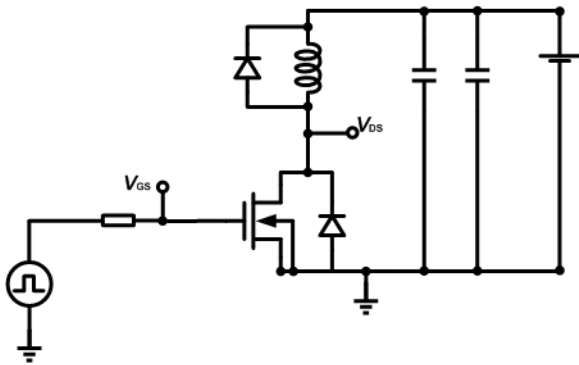
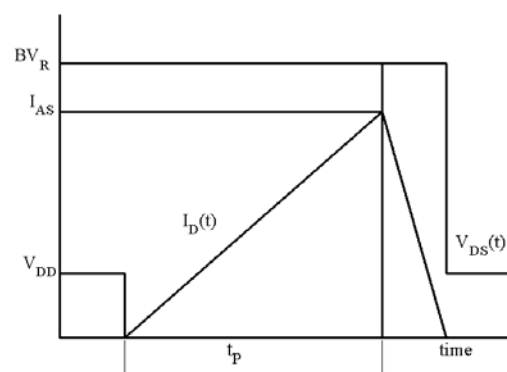
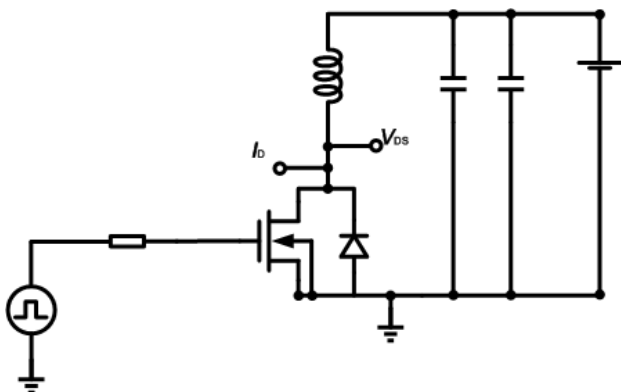


$C=f(V_{DS})$ ;  $V_{GS}=0$ ;  $f=1MHz$

Figure 17: C<sub>OSS</sub> Stored Energy

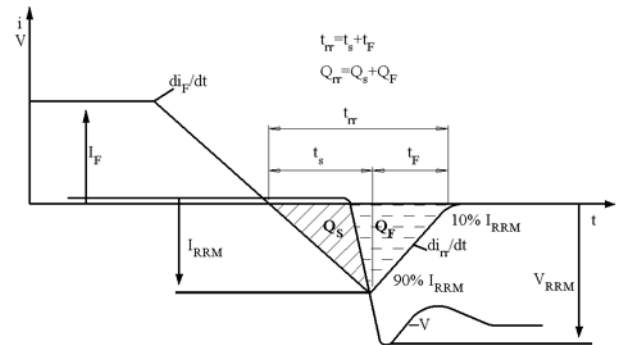
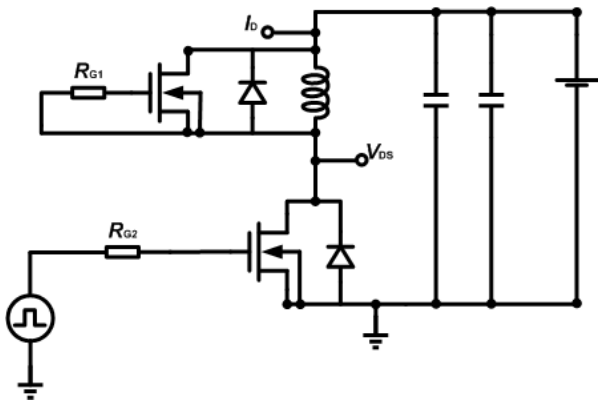


$E_{OSS}=f(V_{DS})$

**Test Circuits**
**1. Gate Charge Test Circuit & Waveform**

**2. Switch Time Test Circuit**

**3. Unclaimed Inductive Switching Test Circuit & Waveforms**


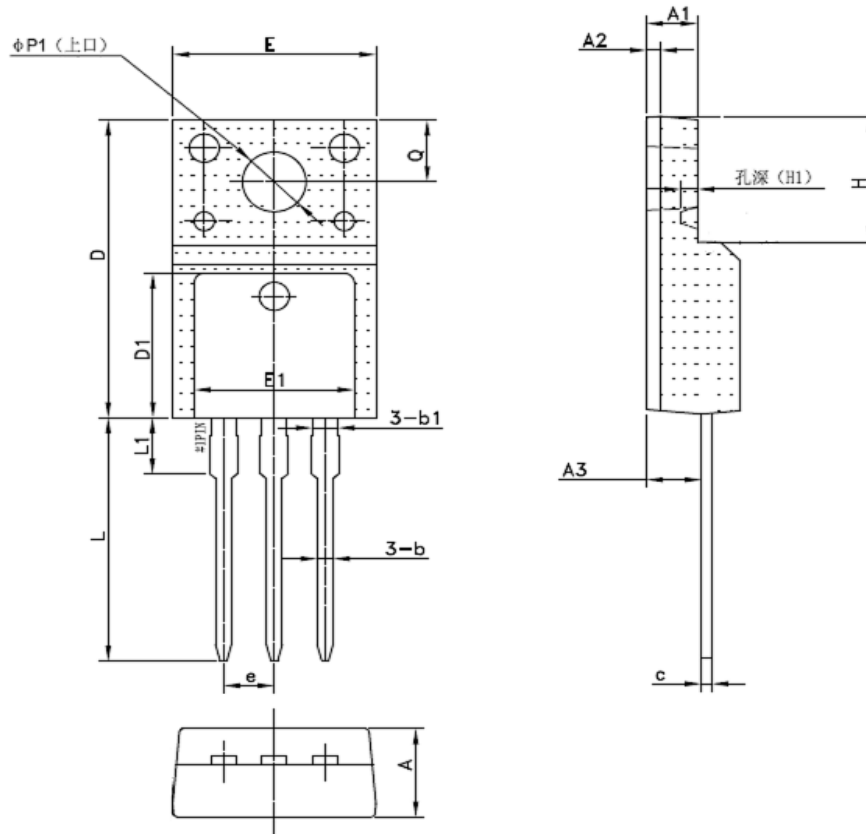


**4. Test Circuit and Waveform for Diode Characteristics**

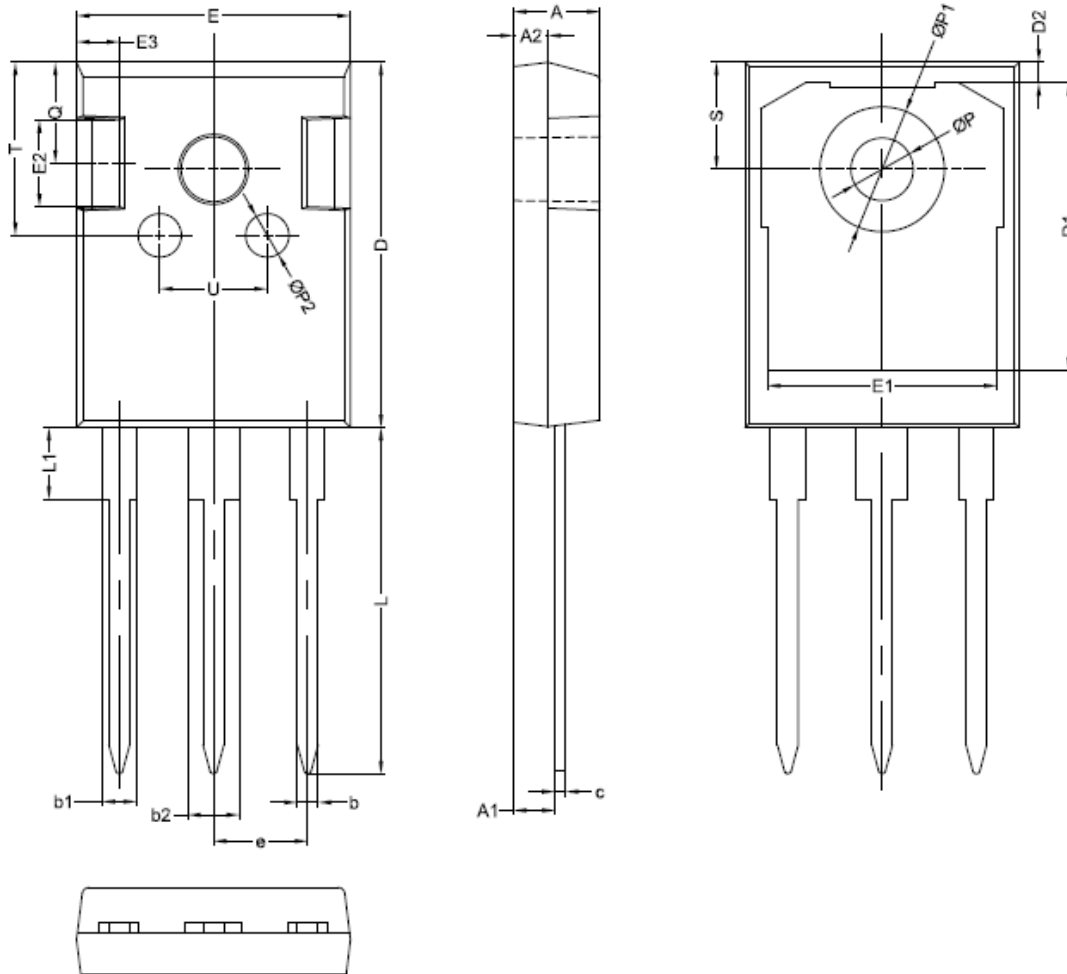


**Mechanical Dimensions**
**TO-220F**

Unit: mm



Symbol	Dimensions(mm)		
	Min.	Typ.	Max.
A	4.30	4.70	4.90
A1	2.34	2.54	2.90
A2	-	0.70	-
A3	2.56	2.76	2.96
b	0.55	-	0.95
b1	-	1.28	-
c	0.42	0.50	0.70
D	14.70	-	16.07
D1	-	7.70	-
E	9.96	10.16	10.36
E1	-	8.00	-
e	2.54(BSC)		
H	-	6.70	-
(H1)	-	(0.81)	-
L	12.48	12.98	13.50
L1	-	2.93	-
ΦP1	-	3.18	-
Q	2.90	3.30	3.50

**Mechanical Dimensions (Continued)**
**TO-247**
**Unit: mm**


Symbol	Dimensions(mm)			Symbol	Dimensions(mm)		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.80	5.00	5.20	E2	-	5.00	-
A1	2.21	2.41	2.61	E3	-	2.50	-
A2	1.90	2.00	2.10	e	5.44(BSC)		
b	1.10	1.20	1.35	L	19.42	19.92	20.42
b1	-	2.00	-	L1	-	4.13	-
b2	-	3.00	-	P	3.50	3.60	3.70
c	0.55	0.60	0.75	P1	-	-	7.40
D	20.80	21.00	21.20	P2	-	2.50	-
D1	-	16.55	-	Q	-	5.80	-
D2	-	1.20	-	S	6.05	6.15	6.25
E	15.60	15.80	16.00	T	-	10.00	-
E1	-	13.30	-	U	-	6.20	-



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